

Maximum Ratings (@T_A = +25 °C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = 25°C T _A = 70°C	I _D	0.65 0.50	А
Maximum Continuous Body Diode Forward Current (Note 6)			Is	0.4	Α
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	4	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P _D	0.29	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	420	°C/W
Total Power Dissipation (Note 6)		P _D	0.35	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	360	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	128	°C/W
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to 150	Ç

Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

D-							
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.8	-	1.6	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		-	0.2	0.4	Ω	$V_{GS} = 10V, I_D = 0.25A$	
Static Drain-Source On-Resistance	l _B	-	0.3	0.7		$V_{GS} = 4.5V, I_D = 0.25A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	-	0.4	1.0		$V_{GS} = 4.0V, I_D = 0.25A$	
		-	0.9	-		$V_{GS} = 2.5V, I_D = 0.01A$	
Diode Forward Voltage	V _{SD}	-	0.8	1.2	V	$V_{GS} = 0V, I_S = 0.23A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	50	-	pF		
Output Capacitance	Coss	-	10	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C_{rss}	-	6.8	-	pF	71 = 1.0WHZ	
Gate Resistance	Rg	-	114	-	Ω	$V_{DS} = V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	0.6	-	nC	V _{DS} = 10V, I _D = 250mA	
Total Gate Charge (V _{GS} = 10V)	Qg	-	1.3	-	nC		
Gate-Source Charge	Qgs	-	0.2	-	nC		
Gate-Drain Charge	Q _{qd}	-	0.1	-	nC		
Turn-On Delay Time	t _{D(on)}	-	2.8	-	ns		
Turn-On Rise Time	tr	-	3.2	-	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $I_{D} = 100mA, RG = 10\Omega$	
Turn-Off Delay Time	t _{D(off)}	-	26.3	-	ns		
Turn-Off Fall Time	t _f	-	22.8	-	ns		

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

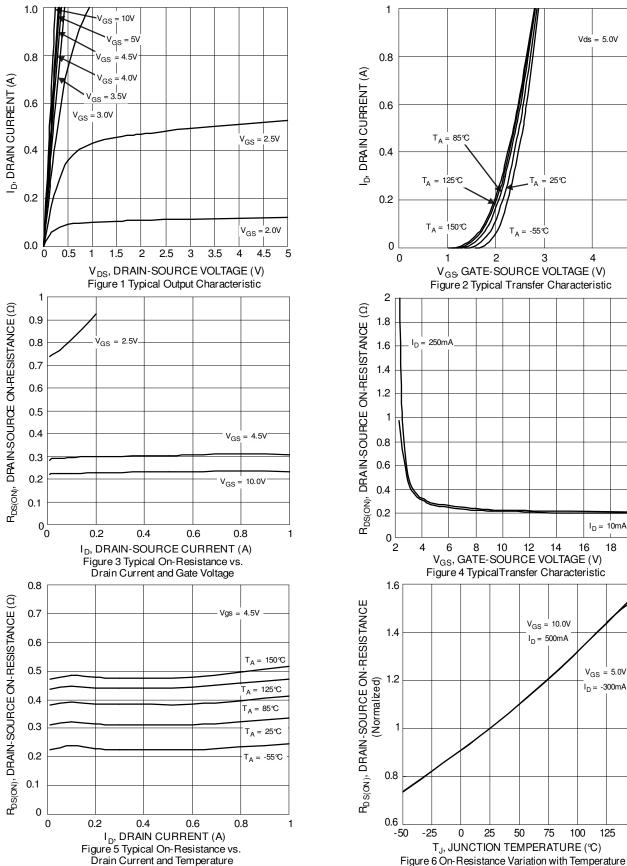
^{6.} Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

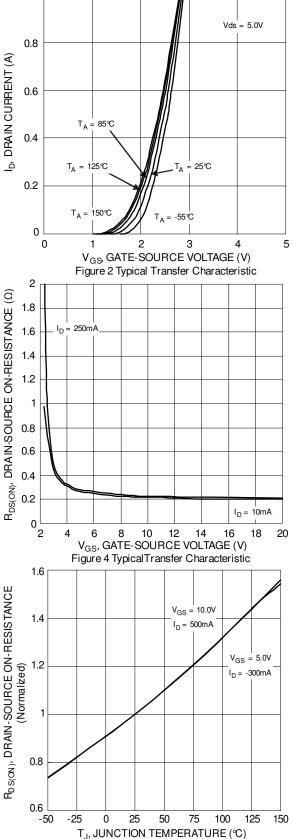
^{7.} Short duration pulse test used to minimize self-heating effect.

^{8.} Guaranteed by design. Not subject to product testing.

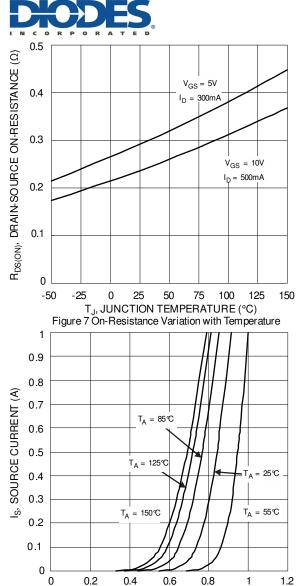


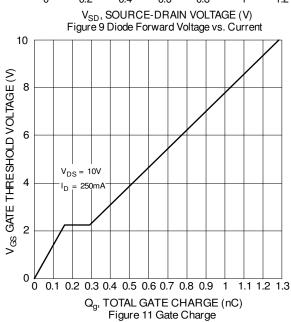


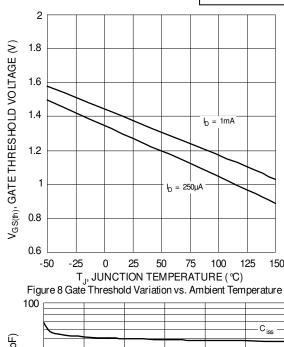


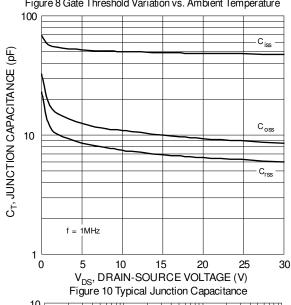


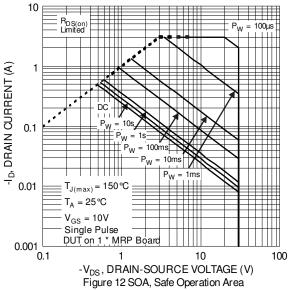
DMN32D4SDW



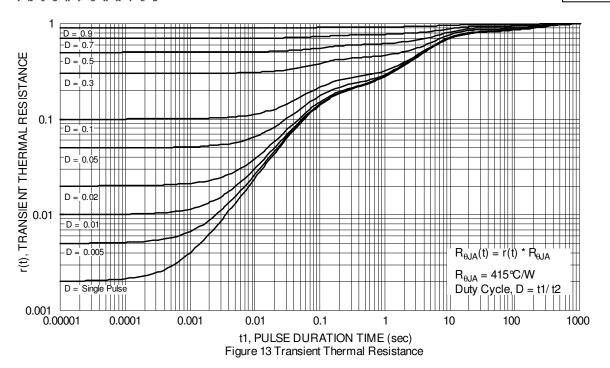






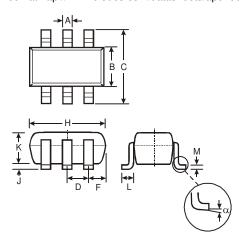






Package Outline Dimensions

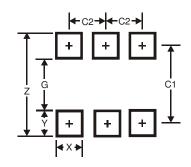
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT363					
Dim	Min	<i>l</i> lin Max Ty			
Α	0.10	0.30	0.25		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	0.65 Typ				
F	0.40	0.45	0.425		
H	1.80	2.20	2.15		
ſ	0	0.10	0.05		
Κ	0.90	1.00	1.00		
٦	0.25	0.40	0.30		
М	0.10	0.22	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.5		
G	1.3		
X	0.42		
Υ	0.6		
C1	1.9		
C2	0.65		



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